# **Hex Gate**

The MC14572UB hex functional gate is constructed with MOS P-channel and N-channel enhancement mode devices in a single monolithic structure. These complementary MOS logic gates find primary use where low power dissipation and/or high noise immunity is desired. The chip contains four inverters, one NOR gate and one NAND gate.

- Diode Protection on All Inputs
- Single Supply Operation
- Supply Voltage Range = 3.0 Vdc to 18 Vdc
- NOR Input Pin Adjacent to VSS Pin to Simplify Use As An Inverter
- NAND Input Pin Adjacent to VDD Pin to Simplify Use As An Inverter
- NOR Output Pin Adjacent to Inverter Input Pin For OR Application
- NAND Output Pin Adjacent to Inverter Input Pin For AND Application
- Capable of Driving Two Low–power TTL Loads or One Low–Power Schottky TTL Load over the Rated Temperature Range

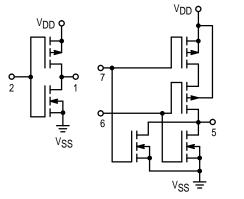
# MAXIMUM RATINGS\* (Voltages Referenced to VSS)

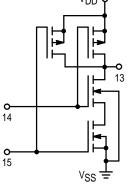
Symbol	Parameter	Value	Unit
V <sub>DD</sub>	DC Supply Voltage	- 0.5 to + 18.0	V
V <sub>in</sub> , V <sub>out</sub>	Input or Output Voltage (DC or Transient)	$-0.5$ to $V_{DD} + 0.5$	V
I <sub>in</sub> , I <sub>out</sub>	Input or Output Current (DC or Transient), per Pin	± 10	mA
PD	Power Dissipation, per Package†	500	mW
T <sub>stg</sub>	Storage Temperature	- 65 to + 150	°C
TL	Lead Temperature (8–Second Soldering)	260	°C

<sup>\*</sup> Maximum Ratings are those values beyond which damage to the device may occur. †Temperature Derating:

Plastic "P and D/DW" Packages: - 7.0 mW/°C From 65°C To 125°C Ceramic "L" Packages: - 12 mW/°C From 100°C To 125°C

# **CIRCUIT SCHEMATIC**





# MC14572UB



L SUFFIX CERAMIC CASE 620



P SUFFIX PLASTIC CASE 648



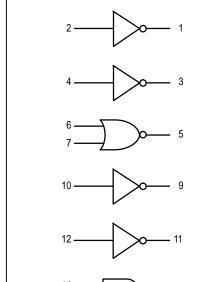
D SUFFIX SOIC CASE 751B

## ORDERING INFORMATION

MC14XXXUBCP Plastic
MC14XXXUBCL Ceramic
MC14XXXUBD SOIC

 $T_A = -55^{\circ}$  to 125°C for all packages.

# **LOGIC DIAGRAM**





**ELECTRICAL CHARACTERISTICS** (Voltages Referenced to V<sub>SS</sub>)

			V <sub>DD</sub>	- 5	5°C		25°C		125	5°C	
Characteristic		Symbol	Vdc	Min	Max	Min	Typ #	Max	Min	Max	Unit
Output Voltage V <sub>in</sub> = V <sub>DD</sub> or 0	"0" Level	VOL	5.0 10 15	_ _ _	0.05 0.05 0.05	_ _ _	0 0 0	0.05 0.05 0.05	_ _ _	0.05 0.05 0.05	Vdc
$V_{in} = 0$ or $V_{DD}$	"1" Level	VOH	5.0 10 15	4.95 9.95 14.95	_ _ _	4.95 9.95 14.95	5.0 10 15	_ _ _	4.95 9.95 14.95	_ _ _	Vdc
Input Voltage (V <sub>O</sub> = 4.5 or 0.5 Vdc) (V <sub>O</sub> = 9.0 or 1.0 Vdc) (V <sub>O</sub> = 13.5 or 1.5 Vdc)	"0" Level	V <sub>I</sub> L	5.0 10 15	_ _ _	1.0 2.0 2.5		2.25 4.50 6.75	1.0 2.0 2.5		1.0 2.0 2.5	Vdc
(V <sub>O</sub> = 0.5 or 4.5 Vdc) (V <sub>O</sub> = 1.0 or 9.0 Vdc) (V <sub>O</sub> = 1.5 or 13.5 Vdc)	"1" Level	VIH	5.0 10 15	4.0 8.0 12.5	_	4.0 8.0 12.5	2.75 5.50 8.25	_ _ _	4.0 8.0 12.5	_	Vdc
Output Drive Current (V <sub>OH</sub> = 2.5 Vdc) (V <sub>OH</sub> = 4.6 Vdc) (V <sub>OH</sub> = 9.5 Vdc) (V <sub>OH</sub> = 13.5 Vdc)	Source	ІОН	5.0 5.0 10 15	- 1.2 - 0.25 - 0.62 - 1.8	_ _ _ _	- 1.0 - 0.2 - 0.5 - 1.5	- 1.7 - 0.36 - 0.9 - 3.5	  -  -	- 0.7 - 0.14 - 0.35 - 1.1	_ _ _ _	mAdc
$(V_{OL} = 0.4 \text{ Vdc})$ $(V_{OL} = 0.5 \text{ Vdc})$ $(V_{OL} = 1.5 \text{ Vdc})$	Sink	lOL	5.0 10 15	0.64 1.6 4.2	_ _ _	0.51 1.3 3.4	0.88 2.25 8.8	_ _ _	0.36 0.9 2.4	_ _ _	mAdc
Input Current		l <sub>in</sub>	15	_	±0.1	_	±0.00001	±0.1	_	±1.0	μAdc
Input Capacitance (V <sub>in</sub> = 0)		C <sub>in</sub>	_	_	_	_	5.0	7.5	_	_	pF
Quiescent Current (Per Package)		I <sub>DD</sub>	5.0 10 15	_ _	0.25 0.5 1.0	_ 	0.0005 0.0010 0.0015	0.25 0.5 1.0	_ _	7.5 15 30	μAdc
Total Supply Current**†  (Dynamic plus Quiescent, Per Package)  (C <sub>L</sub> = 50 pF on all outputs, all buffers switching)		lΤ	5.0 10 15			$I_{T} = (3)$	.89 μΑ/kHz) .80 μΑ/kHz) .68 μΑ/kHz)	f + I <sub>DD</sub>			μAdc

#Data labelled "Typ" is not to be used for design purposes but is intended as an indication of the IC's potential performance.

$$I_T(C_L) = I_T(50 \text{ pF}) + (C_L - 50) \text{ Vfk}$$

where:  $I_T$  is in  $\mu A$  (per package),  $C_L$  in pF,  $V = (V_{DD} - V_{SS})$  in volts, f in kHz is input frequency, and k = 0.006.

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation,  $V_{in}$  and  $V_{out}$  should be constrained to the range  $V_{SS} \leq (V_{in} \text{ or } V_{out}) \leq V_{DD}.$  Unused inputs must always be tied to an appropriate logic voltage level (e.g., either  $V_{SS}$  or  $V_{DD}$ ). Unused outputs must be left open.

#### **PIN ASSIGNMENT** $OUT_A$ INA 15 IN 2<sub>F</sub> 14 | IN 1<sub>F</sub> OUT<sub>B</sub> [ IN<sub>B</sub> [ 13 DUT<sub>F</sub> OUT<sub>C</sub> [ 12 ] INE IN 1<sub>C</sub> 11 OUTE IN 2<sub>C</sub> 10 9 DUTD VSS [

<sup>\*\*</sup>The formulas given are for the typical characteristics only at 25°C.

<sup>†</sup>To calculate total supply current at loads other than 50 pF:

# SWITCHING CHARACTERISTICS\* ( $C_L = 50 \text{ pF}, T_A = 25^{\circ}C$ )

Characteristic	Symbol	V <sub>DD</sub>	Min	Тур#	Max	Unit
Output Rise Time $t_{TLH} = (3.0 \text{ ns/pF}) \text{ C}_L + 30 \text{ ns}$ $t_{TLH} = (1.5 \text{ ns/pF}) \text{ C}_L + 15 \text{ ns}$ $t_{TLH} = (1.1 \text{ ns/pF}) \text{ C}_L + 10 \text{ ns}$	tTLH	5.0 10 15	_ _ _	180 90 65	360 180 130	ns
Output Fall Time t <sub>THL</sub> = (1.5 ns/pF) C <sub>L</sub> + 25 ns t <sub>THL</sub> = (0.75 ns/pF) C <sub>L</sub> + 12.5 ns t <sub>THL</sub> = (0.55 ns/pF) C <sub>L</sub> + 9.5 ns	tTHL	5.0 10 15	_ _ _	100 50 40	200 100 80	ns
Propagation Delay Time $t_{PLH}, t_{PHL} = (1.7 \text{ ns/pF}) \text{ C}_{L} + 5 \text{ ns}$ $t_{PLH}, t_{PHL} = (0.66 \text{ ns/pF}) \text{ C}_{L} + 17 \text{ ns}$ $t_{PLH}, t_{PHL} = (0.5 \text{ ns/pF}) \text{ C}_{L} + 15 \text{ ns}$	<sup>t</sup> PLH <sup>,</sup> <sup>t</sup> PHL	5.0 10 15	_ _ _	90 50 40	180 100 80	ns

<sup>\*</sup> The formulas given are for the typical characteristics only at 25°C.

<sup>#</sup>Data labelled "Typ" is not to be used for design purposes but is intended as an indication of the IC's potential performance.

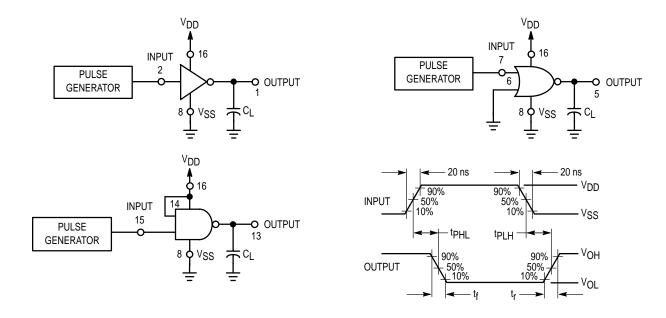
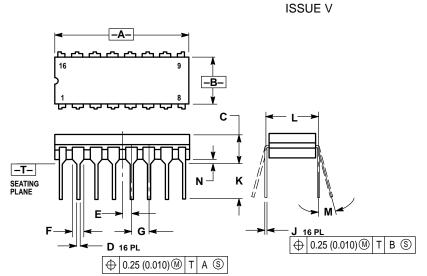


Figure 1. Switching Time Test Circuits and Waveforms

# **OUTLINE DIMENSIONS**

# **L SUFFIX** CERAMIC DIP PACKAGE CASE 620-10



### NOTES:

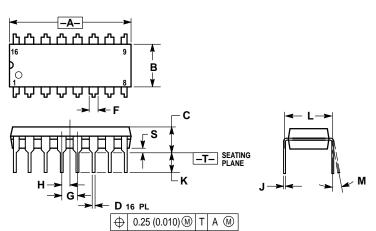
- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

- ANSI Y14.5M, 1982.
  CONTROLLING DIMENSION: INCH.
  DIMENSION L TO CENTER OF LEAD WHEN
  FORMED PARALLEL.
  DIMENSION F MAY NARROW TO 0.76 (0.030)
  WHERE THE LEAD ENTERS THE CERAMIC

	INC	HES	MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
Α	0.750	0.785	19.05	19.93	
В	0.240	0.295	6.10	7.49	
C		0.200		5.08	
D	0.015	0.020	0.39	0.50	
Е	0.050 BSC		1.27 BSC		
F	0.055	0.065	1.40	1.65	
G	0.100 BSC		2.54 BSC		
Н	0.008	0.015	0.21	0.38	
K	0.125	0.170	3.18	4.31	
L	0.300 BSC		7.62 BSC		
M	0 °	15°	0 °	15°	
N	0.020	0.040	0.51	1.01	

# **P SUFFIX**

PLASTIC DIP PACKAGE CASE 648-08 ISSUE R



## NOTES:

- NOTES:

  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

  2. CONTROLLING DIMENSION: INCH.

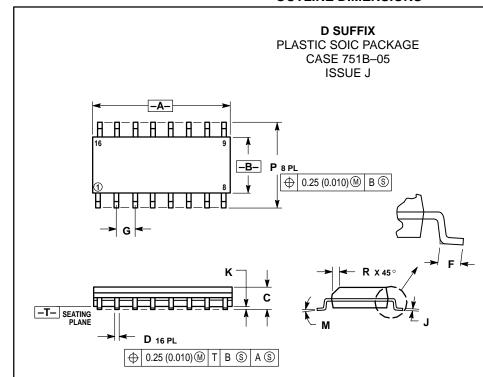
  3. DIMENSION L TO CENTER OF LEADS WHEN FORMED PARALLEL.

  4. DIMENSION B DOES NOT INCLUDE MOLD FLASH.

  5. ROUNDED CORNERS OPTIONAL.

	INC	HES	MILLIMETERS			
DIM	MIN	MAX	MIN	MAX		
Α	0.740	0.770	18.80	19.55		
В	0.250	0.270	6.35	6.85		
С	0.145	0.175	3.69	4.44		
D	0.015	0.021	0.39	0.53		
F	0.040	0.70	1.02	1.77		
G	0.100	BSC	2.54 BSC			
Н	0.050	BSC	1.27 BSC			
J	0.008	0.015	0.21	0.38		
K	0.110	0.130	2.80	3.30		
L	0.295	0.305	7.50	7.74		
M	0°	10°	0°	10 °		
S	0.020	0.040	0.51	1.01		

## **OUTLINE DIMENSIONS**



- DIMENSIONING AND TOLERANCING PER ANSI
- CONTROLLING DIMENSION: MILLIMETER.
- DIMENSIONS A AND B DO NOT INCLUDE
- MOLD PROTRUSION.
  MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
- DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR
  PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIN	IETERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	9.80	10.00	0.386	0.393	
В	3.80	4.00	0.150	0.157	
С	1.35	1.75	0.054	0.068	
D	0.35	0.49	0.014	0.019	
F	0.40	1.25	0.016	0.049	
G	1.27	BSC	0.050 BSC		
Ĺ	0.19	0.25	0.008	0.009	
Κ	0.10	0.25	0.004	0.009	
М	0°	7°	0°	7°	
Р	5.80	6.20	0.229	0.244	
R	0.25	0.50	0.010	0.019	

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